Surface Mount

Monolithic Amplifier

DC-4 GHz

Product Features

- DC-4 GHz
- Single Voltage Supply
- Internally Matched to 50 Ohms
- Unconditionally Stable
- Low Performance Variation Over Temperature
- Transient Protected
- Aqueous washable
- Protected By US Patent 6,943,629

Typical Applications

- Cellular/ PCS/ 3G Base Station
- CATV, Cable Modem & DBS
- Fixed Wireless & WLAN
- Microwave Radio & Test Equipment



CASE STYLE: WW107 PRICE: \$3.90 ea. QTY. (20)

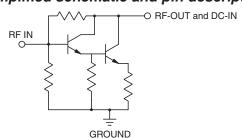
+RoHS Compliant

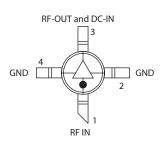
The +Suffix identifies RoHS Compliance. See our web site for RoHS Compliance methodologies and qualifications

General Description

ERA-6SM+ (RoHS compliant) is a wideband amplifier offering high dynamic range. It has repeatable performance from lot to lot. It is enclosed in a Micro-X package. ERA-6SM+ uses Darlington configuration and is fabricated using InGaP HBT technology. Expected MTBF is 350 years at 85°C case temperature.

simplified schematic and pin description





Function	Pin Number	Description
RF IN	1	RF input pin. This pin requires the use of an external DC blocking capacitor chosen for the frequency of operation.
RF-OUT and DC-IN	3	RF output and bias pin. DC voltage is present on this pin; therefore a DC blocking capacitor is necessary for proper operation. An RF choke is needed to feed DC bias without loss of RF signal due to the bias connection, as shown in "Recommended Application Circuit".
GND	2,4	Connections to ground. Use via holes as shown in "Suggested Layout for PCB Design" to reduce ground path inductance for best performance.



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P.O. Box 350166, Brooklyn, New York 11235-0003 (718) 934-4500 Fax (718) 332-4661 The Design Engineers Search Engine Provides ACTUAL Data Instantly at minicipults

IFIRF MICROWAVE COMPONENTS

Electrical Specifications at 25°C and 70mA, unless noted

Parameter		Min.	Тур.	Max.	Units	Cpk
Frequency Range*		DC		4	GHz	
Gain	f=0.1 GHz	12	12.6	13.3	dB	≥ 1.5
Gair	f=1 GHz		12.5			
	f=2 GHz	11.1	11.7	12.3		
	f=3 GHz		11.7			
	f=4 GHz	9.8	10.3	10.8		
Magnitude of Gain Variation versus Temperature	f=0.1 GHz		0.0013	.0025	dB/°C	
(values are negative)	f=1 GHz		0.0018	.0035		
,	f=2 GHz		0.0021	.004		
	f=3 GHz		0.0025	.005		
	f=4 GHz		0.0032	.007	in in	
Input Return Loss	f=0.1 GHz		25		dB	
	f=1 GHz		30			
	f=2 GHz		35 33			
	f=3 GHz f=4 GHz		28			
	f=0.1 GHz		35		dB	
Output Return Loss	f=1 GHz		24		ub	
	f=2 GHz		20			
	f=3 GHz		20			
	f=4 GHz		20			
Reverse Isolation	f=2 GHz	16	19		dB	
Output Power @ 1 dB compression	f=0.1 GHz		17.1		dBm	≥ 1.33
Output Fower @ 1 db compression	f=1 GHz	16	17.2			
	f=2 GHz		17.1			
	f=3 GHz		16.2			
	f=4 GHz		14.7			
Saturated Output Power	f=0.1 GHz		17.1		dBm	
(at 3dB compression)	f=1 GHz		17.2			
(at odb compression)	f=2 GHz		17.7			
	f=3 GHz		17.3			
	f=4 GHz		15.9			
Output IP3	f=0.1 GHz	34	36.5		dBm	≥ 1.33
,	f=1 GHz	33	35			
	f=2 GHz	31	33			
	f=3 GHz		30			
	f=4 GHz		28.5		-ID	
Noise Figure	f=0.1 GHz		4.4	5.2	dB	
	f=1 GHz f=2 GHz		4.4 4.5	5.5		
	f=2 GHz f=3 GHz		4.5	5.5 6		
	f=4 GHz		4.5	6		
Group Delay	f=4 GHz		80	0	psec	
Recommended Device Operating Current	1-2 0112		70		mA	
Device Operating Voltage		4.7	5	5.3	V	≥ 1.5
Device Operating Voltage Device Voltage Variation vs. Temperature at 70mA		7.7	-3.2	0.0	mV/°C	21.5
Device Voltage Variation vs. Current at 25°C			11.8		mV/mA	
Thermal Resistance, junction-to-case ¹			143		°C/W	
mormai riesisianoe, juniciion-to-case			143	<u> </u>	U/VV	

^{*}Guaranteed specification DC-4 GHz. Low frequency cut off determined by external coupling capacitors.

Absolute Maximum Ratings

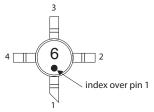
Absolute maximum riatings				
Parameter	Ratings			
Operating Temperature*	-45°C to 85°C			
Storage Temperature	-65°C to 150°C			
Operating Current	85mA			
Power Dissipation	451mW			
Input Power	20dBm			

Note: Permanent damage may occur if any of these limits are exceeded. These ratings are not intended for continuous normal operation. ¹Case is defined as ground leads.

^{*}Based on typical case temperature rise 5°C above ambient.



Product Marking



Markings in addition to model number designation may appear for internal quality control purposes.

Additional Detailed Technical Information

Additional information is available on our web site. To access this information enter the model number on our web site home page.

Performance data, graphs, s-parameter data set (.zip file)

Case Style: WW107

Plastic micro-x, .085 body diameter, lead finish: tin/silver/nickel

Tape & Reel: F4

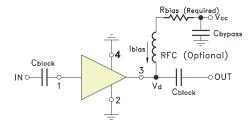
7" Reels with 20, 50, 100, 200, 500, 1K devices 13" Reels with 2K, 4K devices

Suggested Layout for PCB Design: PL-075

Evaluation Board: TB-408-6+

Environmental Ratings: ENV08T2

Recommended Application Circuit



Test Board includes case, connectors, and components (in bold) soldered to PCB

R BIAS				
Vcc	"1%" Res. Values (ohms) for Optimum Biasing			
7	30.1			
8	43.2			
9	56.2			
10	69.8			
11	84.5			
12	100			
13	113			
14	127			
15	140			
16	154			
17	169			
18	182			
19	196			
20	210			

For detailed performance specs

ESD Rating

Human Body Model (HBM): Class 1B (500 v to < 1,000 v) in accordance with ANSI/ESD STM 5.1 - 2001

Machine Model (MM): Class M1 (< 100 v) in accordance with ANSI/ESD STM 5.2 - 1999

MSL Rating

Moisture Sensitivity: MSL1 in accordance with IPC/JEDECJ-STD-020C

No.	Test Required	Condition	Standard	Quantity
1	Visual Inspection	Low Power Microscope Magnification 40x	MIP-IN-0003 (MCT spec)	45 units
2	Electrical Test	Room Temperature	SCD (MCL spec)	45 units
3	SAM Analysis	Less than 10% growth in term of delamination	J-Std-020C (Jedec Standard)	45 units
4	Moisture Sensitivity Level 1	Bake at 125°C for 24 hours Soak at 85°C/85%RH for 168 hours Reflow 3 cycles at 260°C peak	J-Std-020C (Jedec Standard)	45 units

MSL Test Flow Chart

